P2N2222A

Amplifier Transistors

NPN Silicon

Features

- Pb−Free Packages are Available*

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	40	Vdc
Collector – Base Voltage	V_{CBO}	75	Vdc
Emitter – Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	600	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
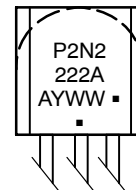
ON Semiconductor®

http://onsemi.com

COLLECTOR
1

2
BASE

3
EMITTER
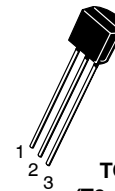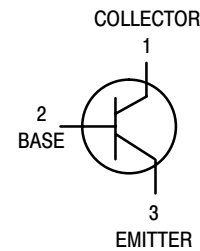
1
2 3
TO−92
(T0−226AA)
CASE 29−11
STYLE 17

MARKING DIAGRAM

P2N2
222A
AYWW ▪

P2N2 = Device Code
222A = Specific Device
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping[†]
P2N2222A	TO−92	5000 Units / Bulk
P2N2222AG	TO−92 (Pb−Free)	5000 Units / Bulk
P2N2222ARL1	TO−92	2000 / Tape & Ammo
P2N2222ARL1G	TO−92 (Pb−Free)	2000 / Tape & Ammo
P2N2222AZL1	TO−92	2000 / Tape & Reel
P2N2222AZL1G	TO−92 (Pb−Free)	2000 Units / Tube

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	75	–	Vdc
Emitter – Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	–	Vdc
Collector Cutoff Current (V_{CE} = 60 Vdc, $V_{EB(off)}$ = 3.0 Vdc)	I_{CEX}	–	10	nAdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	– –	0.01 10	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)	I_{EBO}	–	10	nAdc
Collector Cutoff Current (V_{CE} = 10 V)	I_{CEO}	–	10	nAdc
Base Cutoff Current (V_{CE} = 60 Vdc, $V_{EB(off)}$ = 3.0 Vdc)	I_{BEX}	–	20	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc, T_A = –55°C) (I_C = 150 mAdc, V_{CE} = 10 Vdc) (Note 1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc) (Note 1) (I_C = 500 mAdc, V_{CE} = 10 Vdc) (Note 1)	h_{FE}	35 50 75 35 100 50 40	– – – – 300 – –	–
Collector – Emitter Saturation Voltage (Note 1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{CE(sat)}$	– –	0.3 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	0.6 –	1.2 2.0	Vdc
SMALL – SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (Note 2) (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)C	f_T	300	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	8.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	–	25	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	– –	8.0 4.0	X 10^{-4}
Small – Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	50 75	300 375	–
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	5.0 25	35 200	μMhos
Collector Base Time Constant (I_E = 20 mAdc, V_{CB} = 20 Vdc, f = 31.8 MHz)	$rb'C_c$	–	150	ps
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	N_F	–	4.0	dB

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

P2N2222A

ELECTRICAL CHARACTERISTICS (T$_A$ = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Delay Time	(V$_{CC}$ = 30 Vdc, V$_{BE(off)}$ = −2.0 Vdc,	t$_d$	–	10	ns
Rise Time	I$_C$ = 150 mAdc, I$_{B1}$ = 15 mAdc) (Figure 1)	t$_r$	–	25	ns
Storage Time	(V$_{CC}$ = 30 Vdc, I$_C$ = 150 mAdc,	t$_s$	–	225	ns
Fall Time	I$_{B1}$ = I$_{B2}$ = 15 mAdc) (Figure 2)	t$_f$	–	60	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS

Scope rise time < 4 ns
*Total shunt capacitance of test jig, connectors, and oscilloscope.
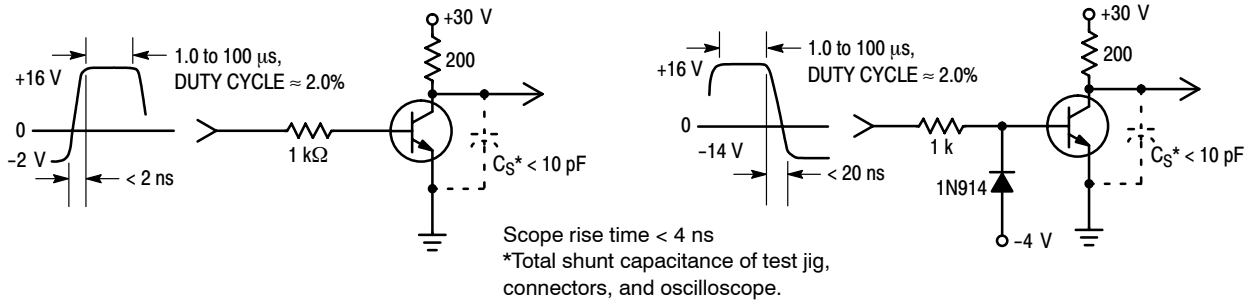
Figure 1. Turn−On Time

Figure 2. Turn−Off Time
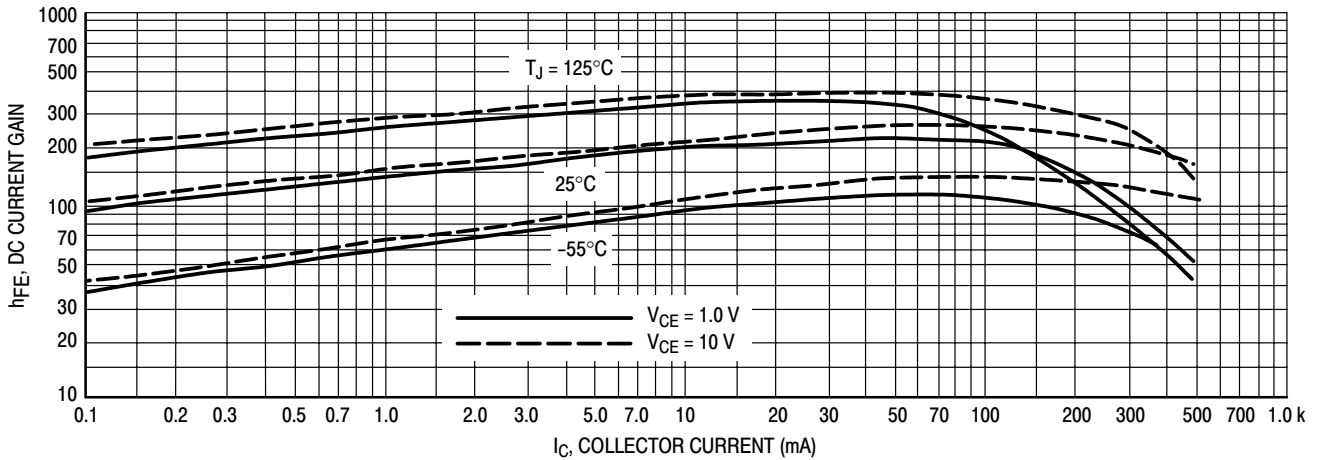
Figure 4. DC Current Gain
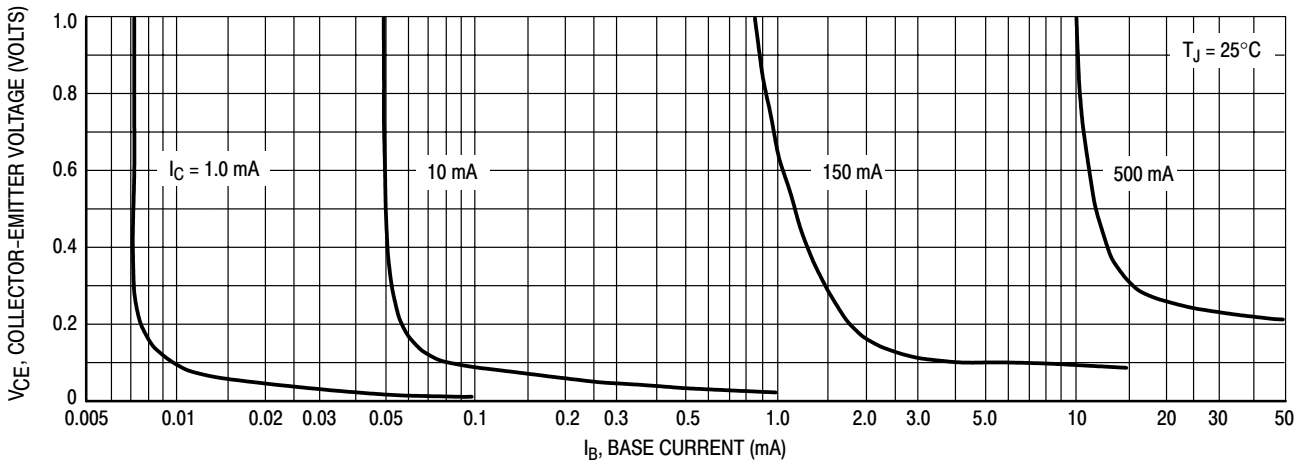
Figure 3. Collector Saturation Region

P2N2222A
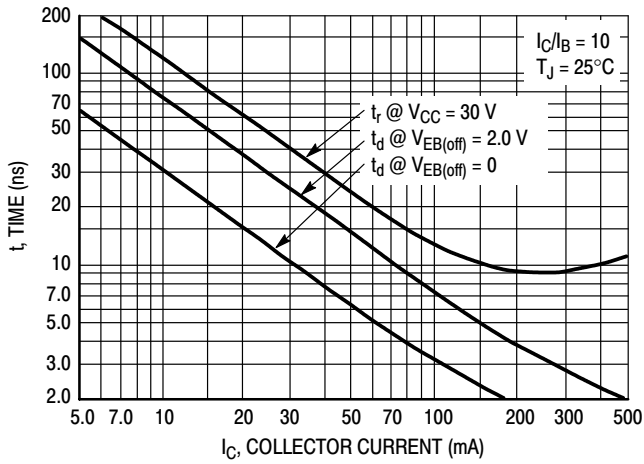
Figure 5. Turn−On Time
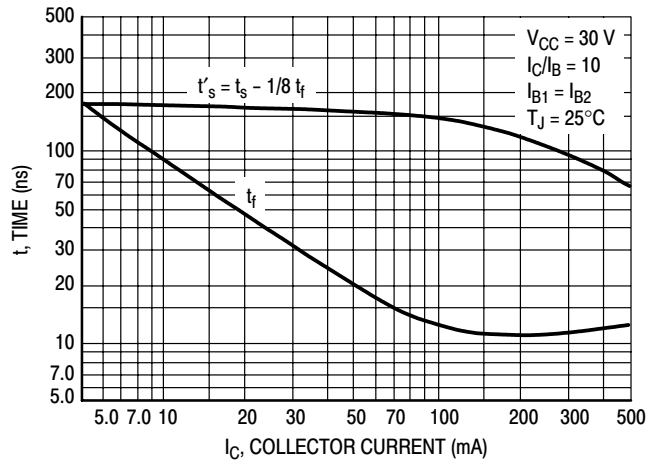
Figure 6. Turn−Off Time
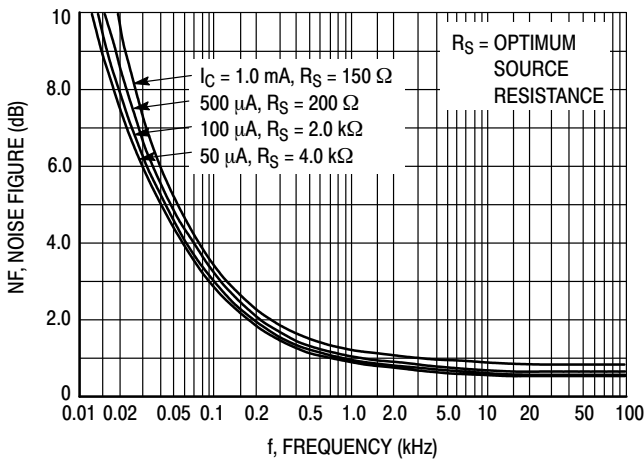
Figure 7. Frequency Effects
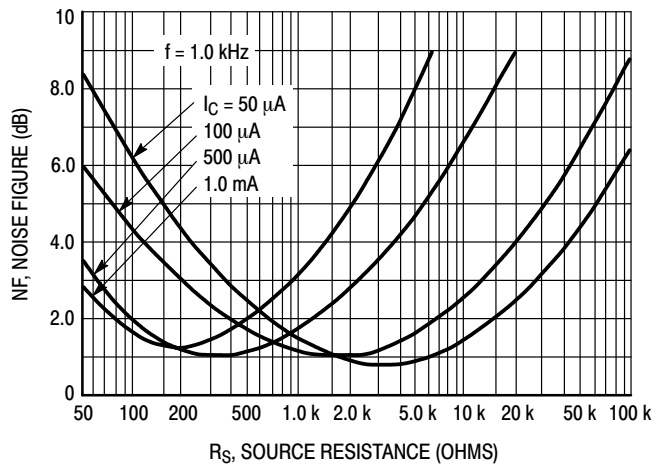
Figure 8. Source Resistance Effects
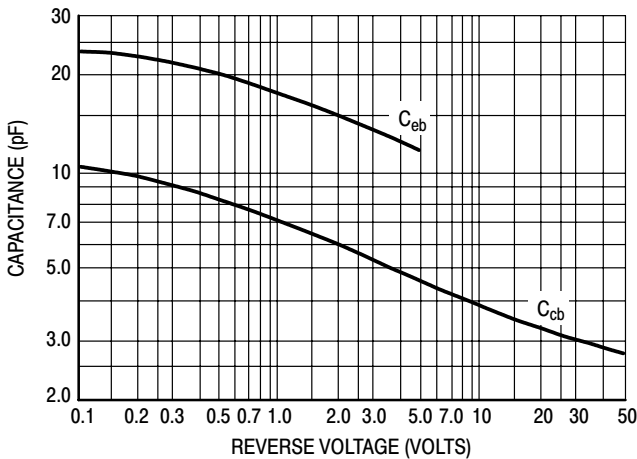
Figure 9. Capacitances
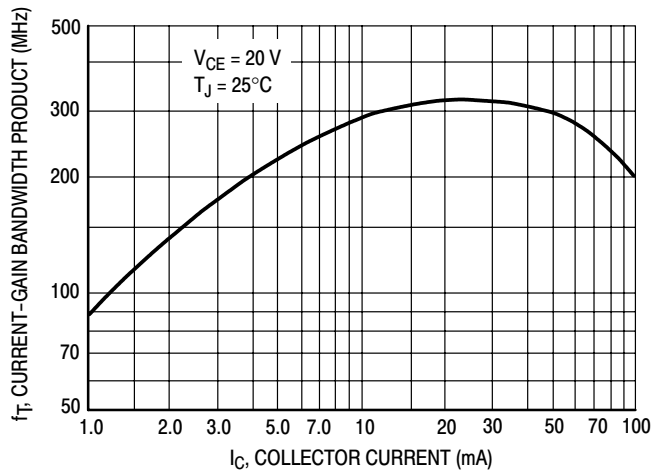
Figure 10. Current−Gain Bandwidth Product
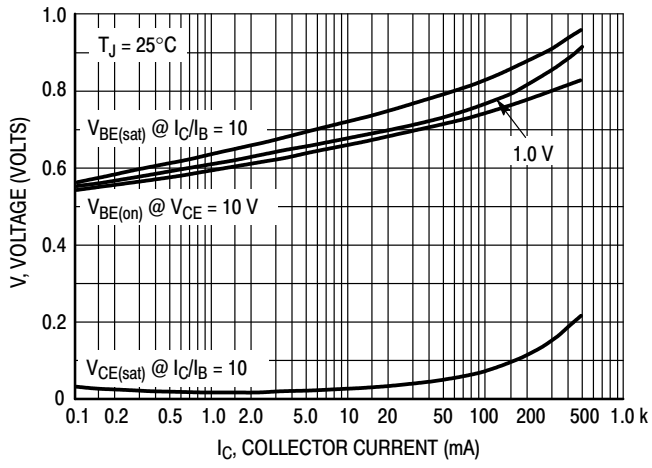
Figure 11. "On" Voltages
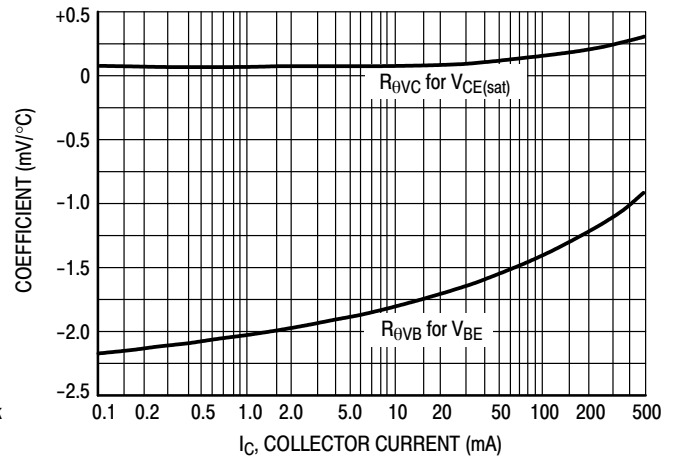
Figure 12. Temperature Coefficients

P2N2222A

PACKAGE DIMENSIONS

TO–92 (TO–226)
CASE 29–11
ISSUE AL
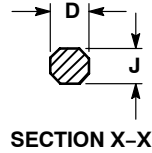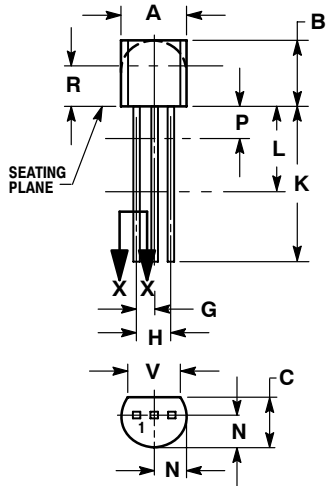
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

SECTION X–X

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 17:
PIN 1. COLLECTOR
    2. BASE
    3. EMITTER

P2N2222A/D